

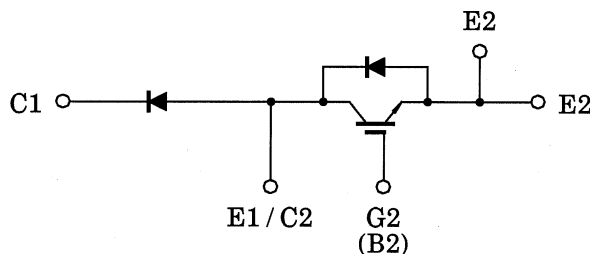
TOSHIBA GTR Module Silicon N Channel IGBT

MG75J1ZS40

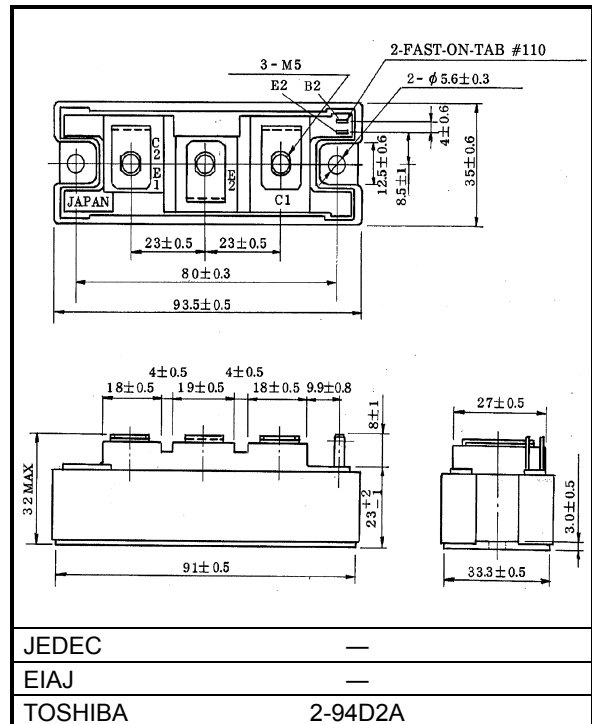
High Power Switching Applications
 Motor Control Applications

- High input impedance
- High speed : $t_f = 0.35\mu s$ (Max)
 $t_{rr} = 0.15\mu s$ (Max)
- Low saturation voltage : $V_{CE(sat)} = 3.5V$ (Max)
- Enhancement-mode
- The electrodes are isolated from case.

Equivalent Circuit



Unit: mm



Weight: 202g

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	600	V
Gate-emitter voltage		V_{GES}	±20	V
Collector current	DC	I_C	75	A
	1ms	I_{CP}	150	
Forward current	DC	I_F	75	A
	1ms	I_{FM}	150	
Collector power dissipation (Tc = 25°C)		P_C	350	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-40 ~ 125	°C
Isolation voltage		V_{isol}	2500 (AC, 1 minute)	V
Screw torque (Terminal / mounting)		—	3 / 3	N·m

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Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA
Collector cut-off current		I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Collector-emitter breakdown voltage		$V_{(BR)CES}$	$I_C = 10mA, V_{GE} = 0$	600	—	—	V
Gate-emitter cut-off voltage		$V_{GE(off)}$	$I_C = 75mA, V_{CE} = 5V$	3.0	—	6.0	V
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 75A, V_{GE} = 15V$	—	2.7	3.5	V
Input capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	6800	—	pF
Switching time	Rise time	t_r		—	0.30	0.60	μs
	Turn-on time	t_{on}		—	0.40	0.80	
	Fall time	t_f		—	0.18	0.35	
	Turn-off time	t_{off}		—	0.60	1.00	
Forward voltage		V_F	$I_F = 75A, V_{GE} = 0$	—	1.7	2.5	V
Reverse recovery time		t_{rr}	$I_F = 75A, V_{GE} = -10V, di/dt = 100A/\mu s$	—	0.08	0.15	μs
Thermal resistance		$R_{th(j-c)}$	Transistor	—	—	0.35	°C/W
			Diode	—	—	0.83	

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